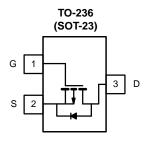


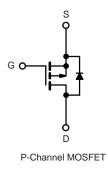
TP0610K-T1-E3-VB Datasheet P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	V _{GS(th)} (V)	I _D (mA)		
- 60	3 at V_{GS} = - 10 V	- 1 to - 3	-500		

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- High-Side Switching
- Low On-Resistance: 3 Ω
- Low Threshold: 2 V (typ.)
- Fast Swtiching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Compliant to RoHS Directive 2002/95/EC





ABSOLUTE MAXIMUM RATINGS $T_A = 25 \degree C$, unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 60	v	
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Durin Currenta	T _A = 25 °C	L_	- 500		
Continuous Drain Current ^a	T _A = 100 °C	Ι _D	- 350	mA	
Pulsed Drain Current ^b		I _{DM}	-1500		
	T _A = 25 °C	Pn	460	mW	
Power Dissipation ^a	T _A = 100 °C	T _A = 100 °C		TIIVV	
Maximum Junction-to-Ambient ^a	·	R _{thJA}	350	°C/W	
Operating Junction and Storage Temperature Range		$T_{J_{J}}T_{stg}$	- 55 to 150	°C	

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

B	® VBsemi
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			Limits				
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = -10 \mu A$	- 60			v	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	- 1		- 3	ľ	
		$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 10 µ		
Gate-Body Leakage		$V_{DS} = 0 V, V_{GS} = \pm 10 V$			± 200	nA	
Gale-body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 10 V, T_{J} = 85 \ ^{\circ}C$			± 500		
		$V_{DS} = 0 V$, $V_{GS} = \pm 5 V$			± 100		
Zara Cata Valtaga Drain Current		$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	- 2		- 25	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 85 ^{\circ}\text{C}$			- 250		
On Chata Duain Quumanti	I _{D(on)}	V _{GS} = - 10 V, V _{DS} = - 4.5 V	- 50				
On-State Drain Current ^a		V _{GS} = - 10 V, V _{DS} = - 10 V	- 600			— mA	
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 25 mA		4			
		V _{GS} = - 10 V, I _D = - 100 mA		3		Ω	
		V_{GS} = - 10 V, I _D = - 100 mA, T _J =125 °C		9			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 100 mA	80			mS	
Diode Forward Voltage	V _{SD}	I _S = - 100 mA, V _{GS} = 0 V			- 1.4	V	
Dynamic							
Total Gate Charge	Qg			2.0		nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -15 \text{ V}$ $I_D \cong -100 \text{ mA}$		1.2			
Gate-Drain Charge	Q _{gd}	B = -100 mA		0.8		1	
Input Capacitance	C _{iss}			23		pF	
Output Capacitance	C _{oss}	$V_{DS} = -25 V, V_{GS} = 0 V$ f = 1 MHz		10			
Reverse Transfer Capacitance	C _{rss}			5			
Switching ^b							
Turn-On Time	t _{d(on)}	$V_{DD} = -25 V, R_1 = 150 \Omega$		20		ns	
Turn-Off Time	t _{d(off)}	$I_D \cong$ - 200 mA, V_{GEN} = - 10 V, R_g = 10 Ω		35			

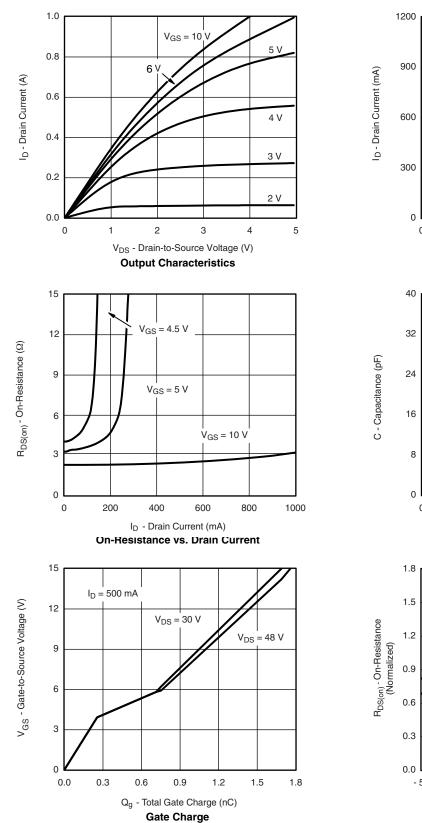
Notes:

a. Pulse test: PW \leq 300 μs duty cycle \leq 2 %.

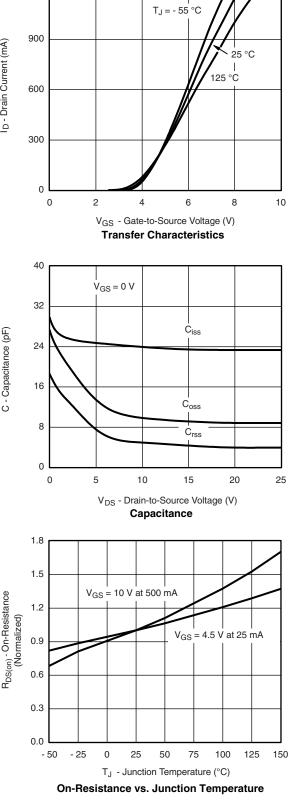
b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





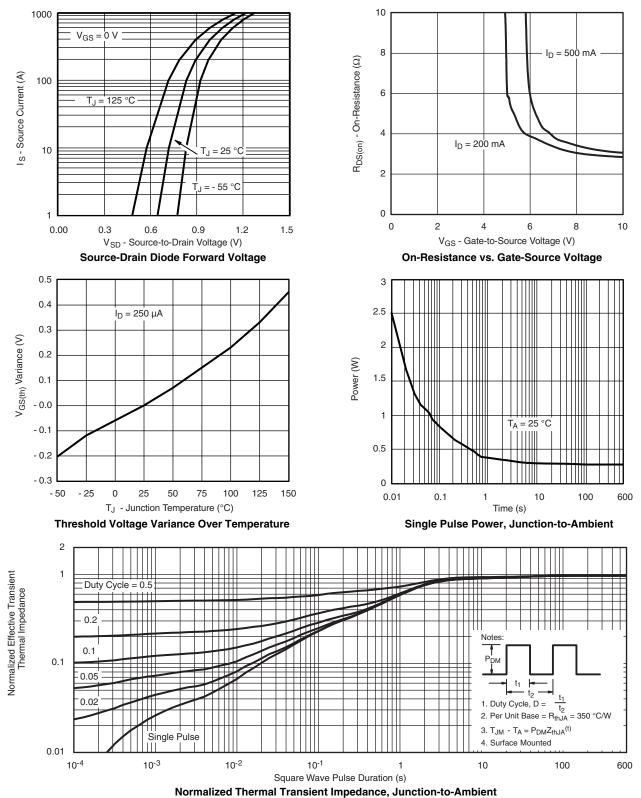
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



服务热线:400-655-8788

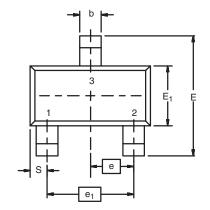


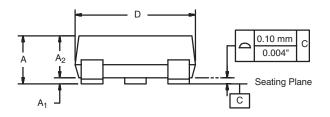
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





SOT-23 (TO-236): 3-LEAD



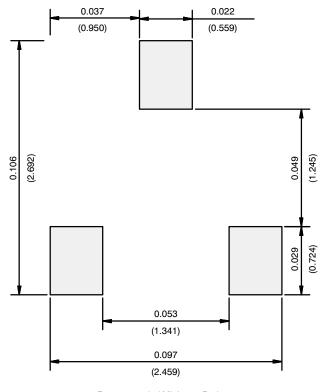




Dim	MILLIMETERS		INCHES		
	Min	Мах	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
C	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01	•	·		



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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